

8 High voltage fast recovery diode for snubber circuit (Non-insulated)

Device type	V _{RRM} Volts	V _{RSM} Volts	I _{F(AV)} Amps.	I _{FSM} Amps.	I ² t A ² s	V _{FM} Volts	I _{RRM} mA	t _{rr} μs	R _{th(j-c)} °C/W	Package	Net weight Grams
ERG28-12	1200	1320	30	500	1000	3.0	10	0.60	0.80	—	25
ERG78-12	1200	1320	30	500	1000	3.0	10	0.60	0.80	—	25
1F60A-120F	1200	1320	60	1000	4000	3.0	20	0.60	0.32	R101	33
1F60A-120R	1200	1320	60	1000	4000	3.0	20	0.60	0.32	R101	33

9 Schottky-barrier diode modules

Device type	V _{RRM} Volts	V _{RSM} Volts	I _{F(AV)} Amps.	I _{FSM} Amps.	I ² t A ² s	V _{FM} Volts	I _{RRM} mA	R _{th(j-c)} °C/W	Package	Net weight Grams	Internal circuit
2BI60E-004	40	48	60 x 2	850	2890	0.58	300	0.5	R205A	110	Fig. 5
2BI100E-004	40	48	100 x 2	1600	10240	0.55	600	0.3	R205A	110	Fig. 5
2BI200E-004C, N, D	40	48	200 x 2 *	3000	36000	0.55	1200	0.15	R208	150	Fig. 5

* I_o

10 Diode and thyristor modules

Device type	Application	Diode and thyristor						Diode V _{FM} Volts	Thyristor		Package	Net weight Grams	Internal circuit
		V _{RRM} Volts	V _{RSM} Volts	I _{F(AV)} Amps.	I _{TSM} Amps.	I ² t A ² s	T _j °C		V _{TM} Volts	I _{GT} mA			
3R3TI20E-080	Power supply for inverter, battery charger and DC motor	800	900	20	400	660	125	Rectifier: 1.20	1.30	80	R611	140	Fig. 6
3R3TI30E-080		800	900	30	600	1490	125		1.40	80	R611	140	Fig. 6
3R3TI60E-080		800	900	60	1000	4150	125		1.30	80	R611	140	Fig. 6
4R3TI20Y-080		800	900	20	400	660	125	Rectifier: 1.20	1.30	80	R701	140	Fig. 7
4R3TI30Y-080		800	900	30	600	1490	125		1.40	80	R701	140	Fig. 7
4R3TI60Y-080		800	900	60	1000	4150	125		1.30	80	R701	140	Fig. 7
6R1TI30Y-080	For dynamic breaking circuit	800	900	30	300	375	125	Output: 1.10	1.40	80	R702	140	Fig. 8

Internal circuit

